

forming an oxide layer overlying the substrate;  
forming a buffer layer overlying the oxide layer;  
thermally annealing the buffer layer to enhance an alignment of  
crystallites of the buffer layer;  
forming a ferroelectric material overlying the substrate;  
forming a gate layer overlying the ferroelectric material, the gate layer  
overlying a channel region; and  
forming a first source/drain region adjacent to a first side of the channel  
region and a second source/drain region adjacent to a second side of the channel region.

2. The method of claim 1 wherein the channel region is about 1  
micron and less.
3. The method of claim 1 wherein the ferroelectric material is a PZT  
bearing compound.
4. The method of claim 1 wherein the buffer layer is a magnesium  
bearing compound.
5. The method of claim 1 wherein the buffer layer is a magnesium  
oxide layer, the magnesium oxide layer being a barrier layer.
6. The method of claim 1 wherein the ferroelectric material has a  
thickness of less than about 1,000 Angstroms.
7. The method of claim 1 wherein the buffer layer has a thickness  
ranging from about 7 to 100 nanometers.
8. The method of claim 1 wherein the ferroelectric material has a  
thickness of about 100 Angstroms and greater.
9. The method of claim 1 wherein the ferroelectric material is PZT.
10. The method of claim 1 wherein the buffer layer is a barrier  
diffusion layer, the barrier diffusion layer substantially preventing diffusion between the  
ferroelectric material to the substrate.
11. The method of claim 1 wherein the buffer material is sputtered  
from a substantially pure magnesium target to form a magnesium oxide layer.

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12. The method of claim 11 wherein the sputtering is maintained at a temperature greater than about 400 degrees Celsius or greater than about 500 degrees Celsius.

13. (Amended) The method of claim 11 wherein the buffer layer is thermally annealed at a temperature of 800-1000 degrees Celsius for about 30 minutes.

14. The method of claim 1 wherein the ferroelectric material is highly oriented.

15. The method of claim 14 wherein the highly oriented material is a polycrystalline film.

16. (Amended) The method of claim 1 wherein the ferroelectric material is substantially free from an amorphous structure.

17. The method of claim 15 wherein the polycrystalline film has a crystal structure of 100 angstroms and greater.

18. (Amended) The method of claim 1 wherein the buffer layer is a template to provide an oriented growth of the ferroelectric material.

19. (Amended) The method of claim 1 wherein the oxide layer is provided by a dry oxidation process comprising an oxygen bearing compound.

20. (Amended) The method of claim 1 wherein the oxide layer passivates the surface of the substrate to protect the channel region.

21. (Amended) A method for fabricating a non-volatile memory device, the method comprising:

providing a substrate;

forming a first buffer layer overlying the substrate;

forming a second buffer layer overlying the first buffer layer;

thermally annealing the second buffer layer to enhance an alignment of crystallites of the second buffer layer;

forming a ferroelectric material overlying the substrate;

forming a gate layer overlying the ferroelectric material, the gate layer overlying a channel region; and

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